

Title	Home institution	Host Institution
Oxide superconductor-ferromagnet heterostructures	National Institute of Materials Physics Bucharest-Magurele (Romania)	Max Planck Institute for intelligent systems (Germany)
PLD growth of epitaxial metal oxide thin films on silicon	Vinča Institute of Nuclear Sciences (Serbia)	Jožef Stefan Institute (JSI), Advanced Materials Department, Ljubljana (Slovenia)
Growth and characterization of Si-doped κ -Ga ₂ O ₃ single domain layers		Paul-Drude-Institut für Festkörperelektronik (Germany)
Study of the compound evaporation thermodynamics by Knudsen Evaporation Mass Spectroscopy	Brno University of Technology (Czech Republic)	Forschungszentrum Jülich GmbH (Germany)
Micro-Photoluminescence measurement of epitaxially grown InAsP Quantum Dots in InP Nanowire	Scuola Normale Superiore, Pisa (Italy)	Wrocław University of Science and Technology (Poland)
Positron annihilation spectroscopy - detection of point defects as a function of the growth regime for β -Ga ₂ O ₃ grown by molecular beam epitaxy	Paul-Drude-Institut für Festkörperelektronik (Germany)	University of Helsinki (Finland)
Comparative study of novel nanocomposite cathodes for solid oxide cells	University of Cambridge (UK)	Catalonia Institute for Energy Research (Spain)
Monitoring the onset of ferroelectricity in nonstoichiometric BaTiO ₃ films using in-situ second harmonic generation	MESA + Institute for Nanotechnology University of Twente (The Netherlands)	ETH Zurich (Switzerland)
Free-standing Ferroelectric Films for Photo-induced Functionalities	Luxembourg Institute of Science and Technology (Luxembourg)	ETH Zurich (Switzerland)
Intermediate-Band Solar Cells (IBSCs) Based on ZnO/CdS/ZnTe Heterojunctions	Moldova State University (Moldova)	National Institute of Materials Physics (Romania)
Virtual substrate for III-V solar cells	L'Institut Photovoltaïque d'Ile-de-France, IPFV-CNRS (France)	Instituto de energía solar (Spain)
Epitaxial growth of hexagonal boron–nitrogen–carbon (h-BNC) monolayer on different substrate materials	Centro de Física de Materiales, San Sebastián (Spain)	Frei Universität Berlin (Germany)
Surface Composition Analysis of Epitaxial Silicon Substrates with Periodic Nano-Size Indents on Surface	Technological University Dublin (Ireland)	National Institute of Materials Physics (Romania)
Epitaxial films of doped HfO ₂ to determine the intrinsic temperature-dependence ferroelectric properties	University of Aveiro (Portugal)	Institute of Materials Science of Barcelona (Spain)
Epitaxial growth of NdFeO ₃ thin films for ultrafast nonlinear phononic applications	IFIMUP, Universidade do Porto (Portugal)	DQMP, University of Geneva (Italy)
The influence of metal surfactants on Ge incorporation in AlGaN – the path to UV emitters	Institute of High Pressure Physics (IHPP) Polish Academy of Sciences (Poland)	Quantum Photonics, Electronics and Engineering Laboratory (France)
Selectivity in magnetic enhanced OER on epitaxial thin film catalysts	University of Twente (The Netherlands)	Helmholtz Zentrum Berlin (Germany)
The growth of NbN/GaN Josephson Junctions	Institute of High Pressure Physics Polish Academy of Sciences (Poland)	Department of Materials Science of the University of Milano-Bicocca (Italy)
Developing of GeSn Avalanche Photodiodes	Politecnico Milano (Italy)	Peter Grünberg Institute 9, Forschungszentrum Jülich (Germany)
Advanced electrochemical characterization of epitaxial multilayers	University of Twente (The Netherlands)	Helmholtz Zentrum Berlin (Germany)

Growth of Complex Antiferromagnetic Oxide Superlattice with Atomically Sharp interfaces	Norwegian University of Science and Technology (Norway)	University of Twente (The Netherlands)
Mapping of Current Pathways in Topology Optimized Magnetoresistive Devices (*)	Technical University of Denmark (Denmark)	University of Basel (Switzerland)
Towards magnetic oxide-topological insulator heterostructures - structural engineering of $\text{La}_{0.7}\text{Sr}_{0.3}\text{MnO}_3$ thin films	Norwegian University of Science and Technology (Norway)	Technical University of Denmark (Denmark)

(*) After being granted, this STSM was cancelled by grantee due to logistic reasons.